

MANUFACTURE OF SEMICONDUCTOR LIGHT-EMITTING ELEMENT

Patent Number: JP11145513

Publication date: 1999-05-28

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Requested Patent: ☐ JP11145513

Application Number: JP19980256249 19980910

Priority Number (s):

IPC

Classification: H01L33/00

EC

Classification:

Equivalents: JP3122644B2

Abstract

PROBLEM TO BE SOLVED: To provide the manufacture of a semiconductor light-emitting element which is capable of manufacturing a flat panel display enabling light emission in multiple colors and having high luminance and high level of fineness.

SOLUTION: A semiconductor layer, consisting of an InGa_N material is laminated on a substrate in the manufacture of the semiconductor light-emitting element, a second semiconductor layer 4 composed of AlN or In_yGa_{1-y}N ($0 \leq y \leq 1$) grown at a temperature lower than a first semiconductor layer, is formed onto a first semiconductor layer 3 consisting on In_xGa_{1-x}N ($0 \leq x \leq 1$), and a third semiconductor layer 5, consisting of In_zGa_{1-z}N ($0 \leq z \leq 1$) grown at a temperature higher than that of the second semiconductor layer is formed on the second semiconductor layer.

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